L Number	Hits	Search Text	DB	Time stamp
1	8	9410821, "9410822"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 09:43
2	1	(9410821, "9410822") and gas adj2 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 09:52
3	1	(9410821, "9410822") and gas near3 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 09:51
6	0	(mosfet with gas adj2 sensor) and hot$plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
7	0	(mosfet with gas adj2 sensor) and hotplate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 09:51
9	16	(hotplate and chemical adj sensor) and gas near3 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:02
10	13	(hotplate and chemical adj sensor) and gas adj2 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:27
11	18	(hotplate and chemical adj sensor) and membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:18
12	0	(mosfet with gas adj2 sensor) and 219/461	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:07
13	0	(hotplate and chemical adj sensor) and 219/461	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:07

15	17	((mosfet with gas adj2 sensor) and membrane) and chemical adj2 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
14	18	(mosfet with gas adj2 sensor) and membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:12
16	15	((hotplate and chemical adj sensor) and gas near3 sensor) and membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:59
4	1	(9410821, "9410822") and gas with sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:25
17	13	(hotplate and chemical adj sensor) and gas adj sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
20	0	(219/461 and hot$plate) and gas adj sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
21	0	(219/461 and hot$plate) and chemical adj2 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
19	42	219/461 and hot$plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:36
22	1	(219/461 and hot$plate) and membrane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:37
23	22	(219/461 and hot$plate) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:45

24	0	((219/461 and hot$plate) and sensor) and micro	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:39
25	0	((219/461 and hot$plate) and membrane) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:46
5	40	mosfet with gas adj2 sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:48
26	0	(((hotplate and chemical adj sensor) and gas near3 sensor) and membrane) and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:58
27	0	((mosfet with gas adj2 sensor) and membrane) and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:59
28	0	((hotplate and chemical adj sensor) and membrane) and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:59
29	0	(hotplate and chemical adj sensor) and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:59
30	0	(9410821, "9410822") and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 10:59
31	6	hotplate and membrane with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:04
32	0	(hotplate and membrane with insulator) and masking and etching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:06

33	2	(hotplate and membrane with insulator) and etching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:05
34	361418	(hotplate and membrane with insulator) and masking or etching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:06
35	0	(hotplate and membrane with insulator) and masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:07
36	0	(mosfet with gas adj2 sensor) and masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:07
37	6	219/461 and masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:09
38	13	(hotplate and chemical adj sensor) and masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:09
39	0	hotplate same sensor same masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:17
40	18	hotplate same masking	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:21
41	4	((219/461 and hot$plate) and sensor) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:24
42	0	((hotplate and chemical adj sensor) and gas adj2 sensor) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:24

43	1	(hotplate and chemical adj sensor) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:25
8	24	hotplate and chemical adj sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:50
18	269	219/461	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 11:52
44	12	(((hotplate and chemical adj sensor) and gas near3 sensor) and membrane) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:11
45	1	((((hotplate and chemical adj sensor) and gas near3 sensor) and membrane) and substrate) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:12
46	1	(hotplate and chemical adj sensor) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:13
47	1	((hotplate and chemical adj sensor) and gas near3 sensor) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:15
48	0	(mosfet with gas adj2 sensor) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:13
49	5839	semiconductor with silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:14
50	6	(semiconductor with silicon adj carbide) and hotplate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:15

51	12	(semiconductor with silicon adj carbide) and hot$plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:32
52	49	4203138, "4234361"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:35
54	10	((4203138, "4234361") and hydroxide) and ion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:38
55	2	((4203138, "4234361") and hydroxide) and etching with ion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:51
53	13	(4203138, "4234361") and hydroxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:38
56	23	(mosfet with gas adj2 sensor) and sensor with metal adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:52
57	21	((mosfet with gas adj2 sensor) and sensor with metal adj oxide) and sensor with polymer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 12:52